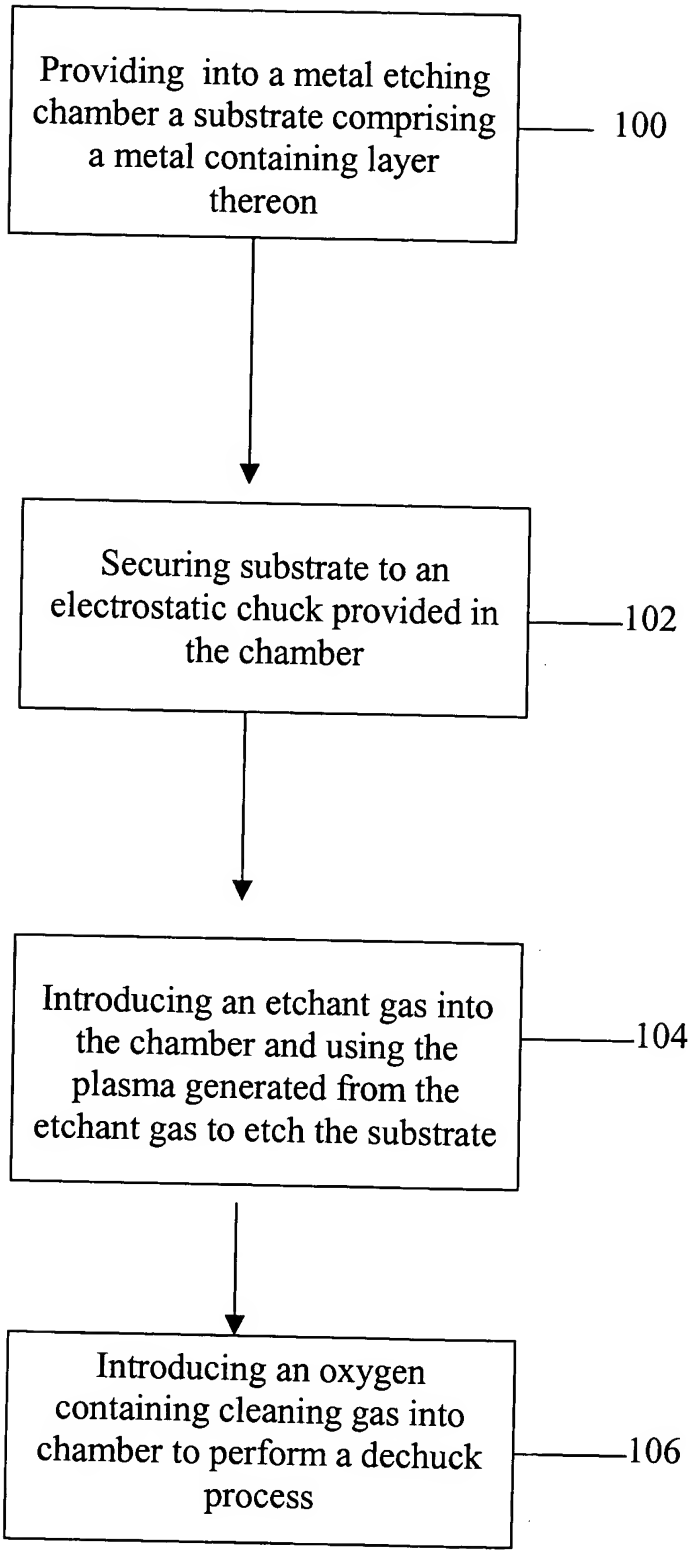
Providing into a metal etching chamber a substrate comprising a metal containing layer thereon
100
Securing substrate to an electrostatic chuck provided in the chamber
102
Introducing an etchant gas into the chamber and using the plasma generated from the etchant gas to etch the substrate
104
Introducing an oxygen containing cleaning gas into chamber to perform a dechuck process
106

Figure 1